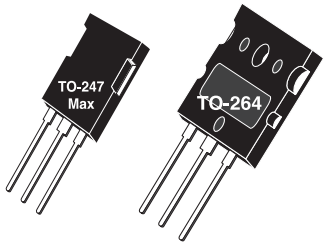
APT85GR120B2
APT85GR120L

1200V, 85A, $V_{ce(on)}$ = 2.5V Typical

Ultra Fast NPT - IGBT®



The Ultra Fast NPT - IGBT® is a new generation of high voltage power IGBTs. Using Non-Punch-Through Technology, the Ultra Fast NPT-IGBT® offers superior ruggedness and ultrafast switching speed.

Features

- **Low Saturation Voltage**
- **Low Tail Current**
- **RoHS Compliant**
- **Short Circuit Withstand Rated**
- **High Frequency Switching**
- **Ultra Low Leakage Current**

Unless stated otherwise, Microsemi discrete IGBTs contain a single IGBT die. This device is recommended for applications such as induction heating (IH), motor control, general purpose inverters and uninterruptible power supplies (UPS).

MAXIMUM RATINGS

All Ratings: T_C = 25°C unless otherwise specified.

Symbol	Parameter	Ratings	Unit
V_{ces}	Collector Emitter Voltage	1200	V
V_{GE}	Gate-Emitter Voltage	±30	
I_{C1}	Continuous Collector Current @ T_C = 25°C	170	A
I_{C2}	Continuous Collector Current @ T_C = 100°C	85	
I_{CM}	Pulsed Collector Current ①	340	
SCWT	Short Circuit Withstand Time: V_{CE} = 600V, V_{GE} = 15V, T_C=125°C	10	µs
P_D	Total Power Dissipation @ T_C = 25°C	962	W
T_J,T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	°C
T_L	Max. Lead Temp. for Soldering: 0.063" from Case for 10 Sec.	300	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Min	Typ	Max	Unit
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage (V_{GE} = 0V, I_C = 1.0mA)	1200			Volts
$V_{GE(TH)}$	Gate Threshold Voltage (V_{CE} = V_{GE}, I_C = 2.5mA, T_j = 25°C)	3.5	5.0	6.5	
$V_{CE(ON)}$	Collector-Emitter On Voltage (V_{GE} = 15V, I_C = 85A, T_j = 25°C)		2.5	3.2	
	Collector-Emitter On Voltage (V_{GE} = 15V, I_C = 85A, T_j = 125°C)		3.3		
	Collector-Emitter On Voltage (V_{GE} = 15V, I_C = 170A, T_j = 25°C)		3.5		
I_{CES}	Collector Cut-off Current (V_{CE} = 1200V, V_{GE} = 0V, T_j = 25°C) ②		10	1000	µA
	Collector Cut-off Current (V_{CE} = 1200V, V_{GE} = 0V, T_j = 125°C) ②		100		
I_{GES}	Gate-Emitter Leakage Current (V_{GE} = ±20V)			±250	nA

CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

DYNAMIC CHARACTERISTICS

APT85GR120B2_L

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	Capacitance		8400		pF
C_{oes}	Output Capacitance	V_{GE} = 0V, V_{CE} = 25V		725		
C_{res}	Reverse Transfer Capacitance	f = 1MHz		190		
V_{GEP}	Gate to Emitter Plateau Voltage	Gate Charge		7.5		V
Q_g ③	Total Gate Charge	V_{GE} = 15V		490	660	nC
Q_{ge}	Gate-Emitter Charge	V_{CE}= 600V		60	85	
Q_{gc}	Gate- Collector Charge	I_C = 85A		230	320	
$t_{d(on)}$	Turn-On Delay Time	Inductive Switching (25°C)		43		ns
t_r	Current Rise Time	V_{CC} = 600V		70		
$t_{d(off)}$	Turn-Off Delay Time	V_{GE} = 15V		300		
t_f	Current Fall Time	I_C = 85A		85		
E_{on2} ⑤	Turn-On Switching Energy	R_G = 4.3 Ω④		6000	9000	µJ
E_{off} ⑥	Turn-Off Switching Energy	T_J = +25°C		3800	5700	
$t_{d(on)}$	Turn-On Delay Time	Inductive Switching (125°C)		43		ns
t_r	Current Rise Time	V_{CC} = 600V		70		
$t_{d(off)}$	Turn-Off Delay Time	V_{GE} = 15V		350		
t_f	Current Fall Time	I_C = 85A		95		
E_{on2} ⑤	Turn-On Switching Energy	R_G = 4.3 Ω④		7800	11,700	µJ
E_{off} ⑥	Turn-Off Switching Energy	T_J = +125°C		4900	7350	

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic		Min	Typ	Max	Unit
$R_{\theta JC}$	Junction to Case Thermal Resistance (IGBT)				.13	°C/W
$R_{\theta JA}$	Junction to Ambient Thermal Resistance				40	
W_T	Package Weight	B2		.22		oz
				6		g
		L		.36		oz
				10		g

1 Repetitive Rating: Pulse width and case temperature limited by maximum junction temperature.

2 Pulse test: Pulse Width < 380μs, duty cycle < 2%.

3 See Mil-Std-750 Method 3471.

4 R_G is external gate resistance, not including internal gate resistance or gate driver impedance. (MIC4452)

5 E_{on2} is the clamped inductive turn on energy that includes a commutating diode reverse recovery current in the IGBT turn on energy loss. A combi device is used for the clamping diode.

6 E_{off} is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1.

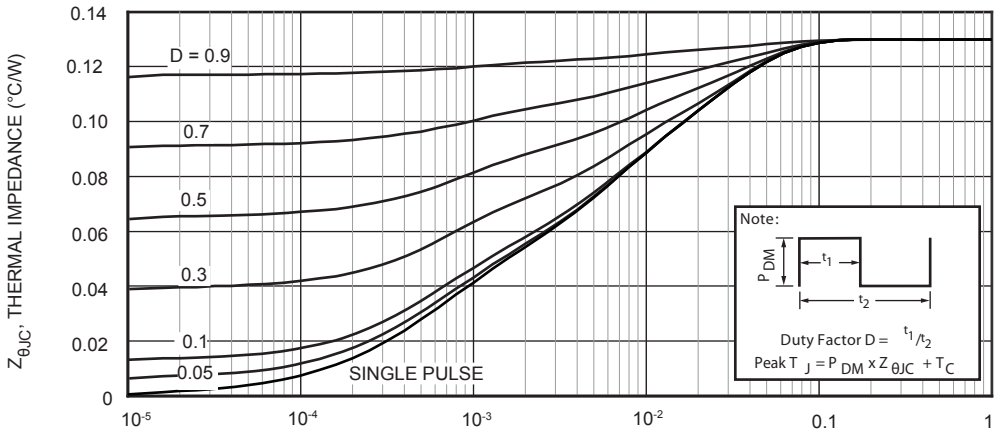


Figure 1, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

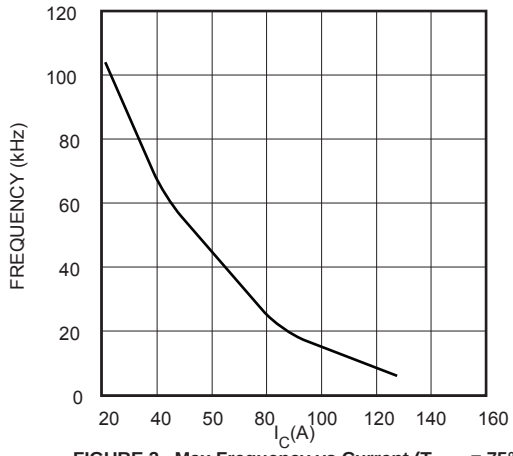


FIGURE 2, Max Frequency vs Current (T_{case} = 75°C)

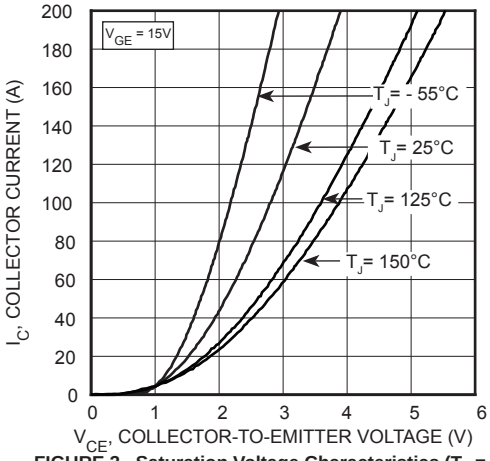


FIGURE 3, Saturation Voltage Characteristics (T_J = 25°C)

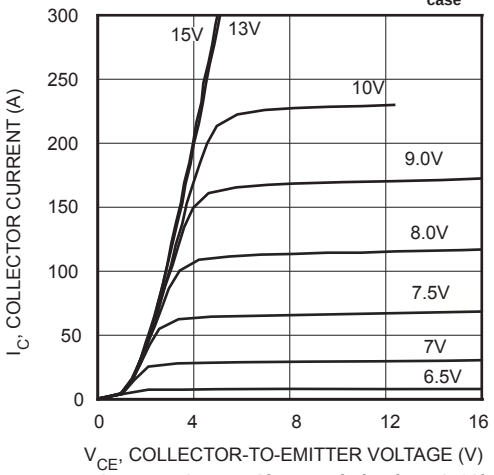


FIGURE 4, Output Characteristics (T_J = 25°C)

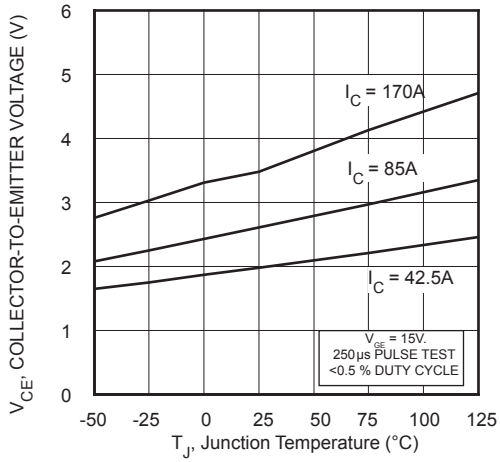


FIGURE 5, On State Voltage vs Junction Temperature

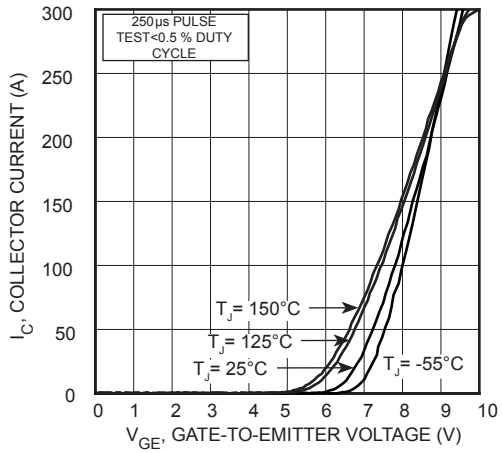


FIGURE 6, Transfer Characteristics

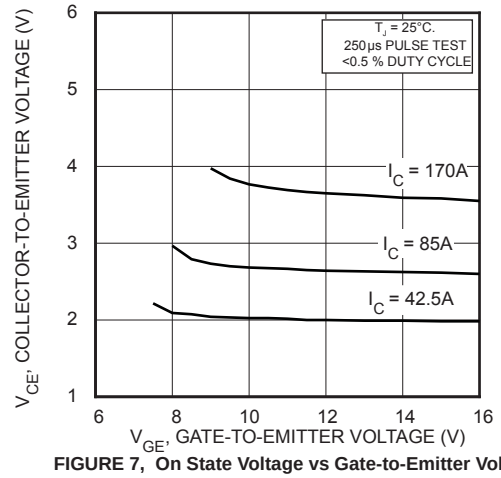


FIGURE 7, On State Voltage vs Gate-to-Emitter Voltage

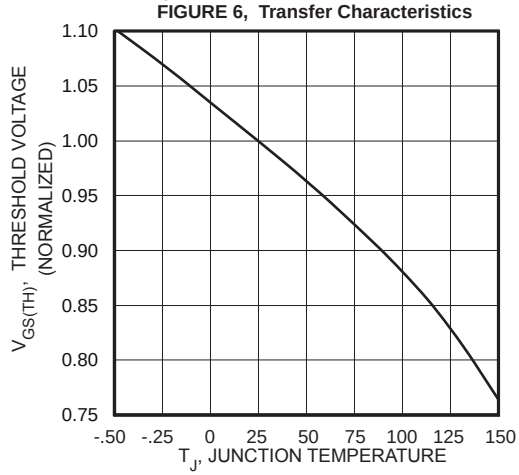


FIGURE 8, Threshold Voltage vs Junction Temperature

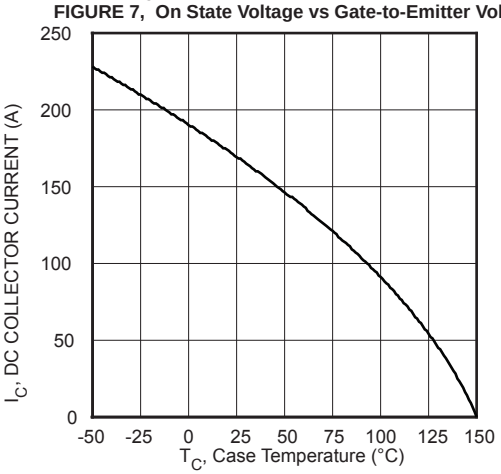


FIGURE 9, DC Collector Current vs Case Temperature

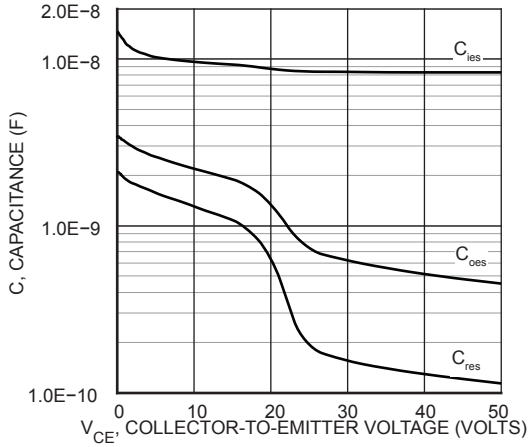


FIGURE 10, Capacitance vs Collector-To-Emitter Voltage

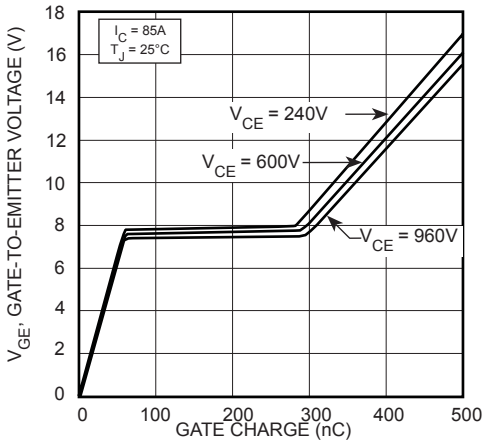


FIGURE 11, Gate charge

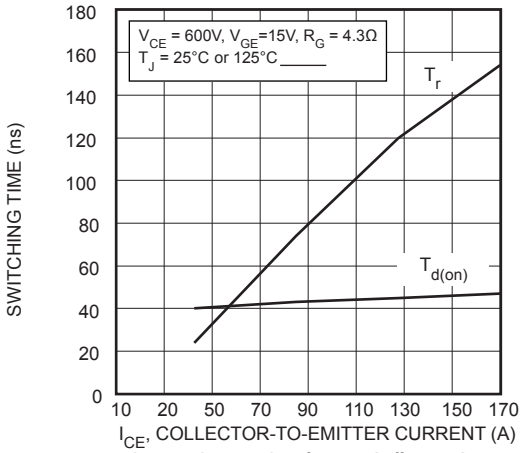


FIGURE 12, Turn-On Time vs Collector Current

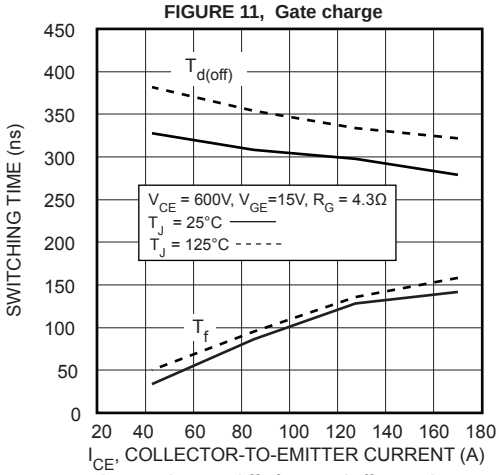


FIGURE 13, Turn-Off Time vs Collector Current

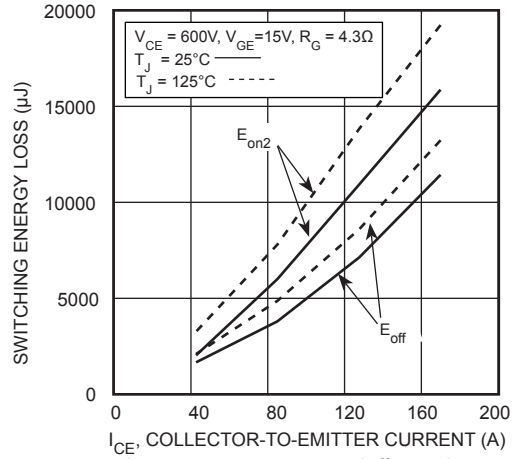


FIGURE 14, Energy Loss vs Collector Current

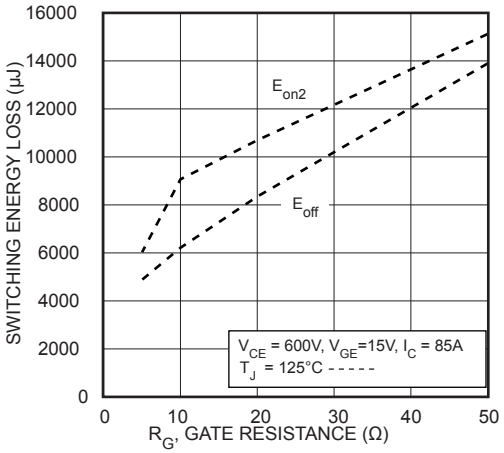


FIGURE 15, Energy Loss vs Gate Resistance

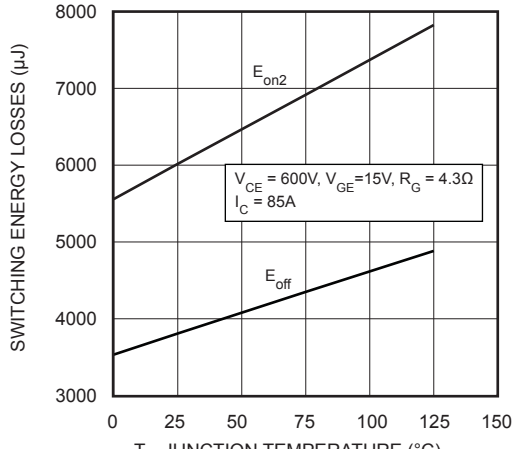


FIGURE 16, Swiitching Energy vs Junction Temperature

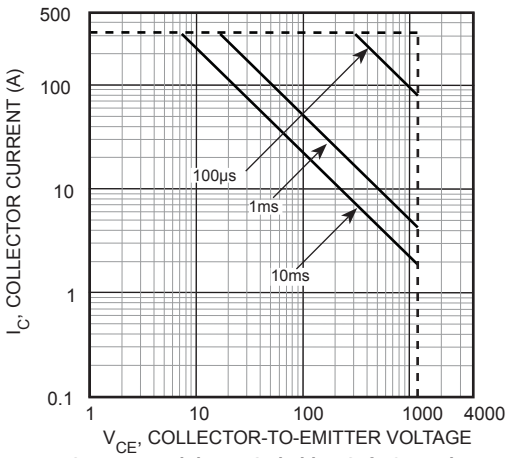
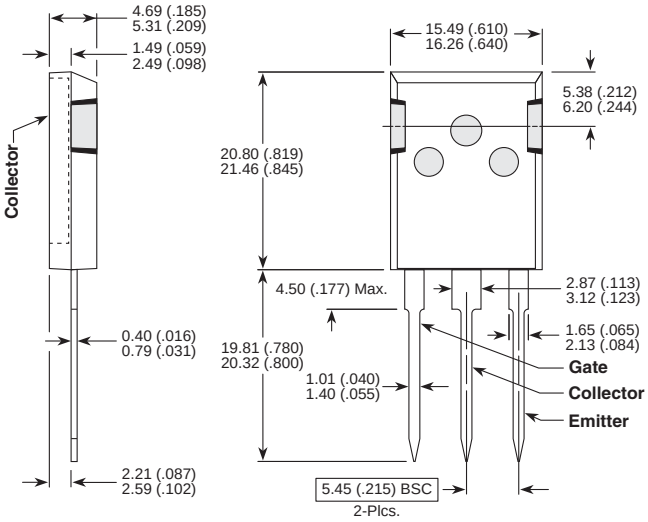


FIGURE 17, Minimum Switching Safe Operating Area

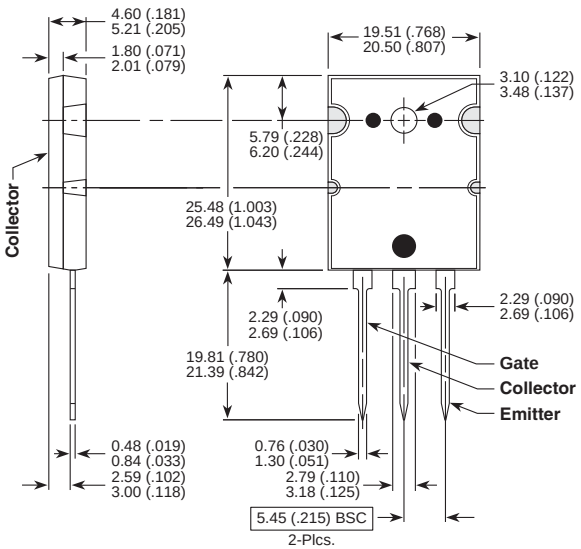
T-MAX™ (B2) Package Outline



These dimensions are equal to the TO-247 without the mounting hole.

Dimensions in Millimeters and (Inches)

TO-264 (L) Package Outline



Dimensions in Millimeters and (Inches)

052-6402 Rev A 8-2012

052-6402 Rev A 8-2012

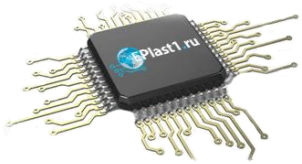
Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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